

SUNSTAR 商斯达实业集团是集研发、生产、工程、销售、代理经销、技术咨询、信息服务等为一体的高科技企业，是专业高科技电子产品生产厂家，是具有10多年历史的专业电子元器件供应商，是中国最早和最大的仓储式连锁规模经营大型综合电子零部件代理分销商之一，是一家专业代理和分销世界各大品牌IC芯片和电子元器件的连锁经营综合性国际公司，专业经营进口、国产名厂名牌电子元件，型号、种类齐全。在香港、北京、深圳、上海、西安、成都等全国主要电子市场设有直属分公司和产品展示展销窗口门市部专卖店及代理分销商，已在全国范围内建成强大统一的供货和代理分销网络。我们专业代理经销、开发生产电子元器件、集成电路、传感器、微波光电元器件、工控机/DOC/DOM电子盘、专用电路、单片机开发、MCU/DSP/ARM/FPGA软件硬件、二极管、三极管、模块等，是您可靠的一站式现货配套供应商、方案提供商、部件功能模块开发配套商。商斯达实业公司拥有庞大的资料库，有数位毕业于著名高校——有中国电子工业摇篮之称的西安电子科技大学（西军电）并长期从事国防尖端科技研究的高级工程师为您精挑细选、量身订做各种高科技电子元器件，并解决各种技术问题。

微波光电部专业研制、代理经销高频、微波、光纤、光电元器件、组件、部件、模块、整机；电磁兼容元器件、材料、设备；微波CAD、EDA软件、开发测试仿真工具；微波、光纤仪器仪表。欢迎国外高科技微波、光纤厂商将优秀产品介绍到中国、共同开拓市场。长期大量现货专业批发高频、微波、卫星、光纤、电视、CATV器件：晶振、VCO、连接器、PIN开关、变容二极管、开关二极管、低噪晶体管、功率电阻及电容、放大器、功率管、MMIC、混频器、耦合器、功分器、振荡器、合成器、衰减器、滤波器、隔离器、环行器、移相器、调制解调器；光电子元件和组件：红外发射管、红外接收管、光电开关、光敏管、发光二极管和发光二极管组件、半导体激光二极管和激光器组件、光电探测器和光接收组件、光发射接收模块、光纤激光器和光放大器、光调制器、光开关、DWDM用光发射和接收器件、用户接入系统光收发器件与模块、光纤连接器、光纤跳线/尾纤、光衰减器、光纤适配器、光隔离器、光耦合器、光环行器、光复用器/转换器；无线收发芯片和模组、蓝牙芯片和模组。

更多产品请看本公司产品专用销售网站：[欢迎索取免费详细资料、设计指南和光盘；产品凡多，未能尽录，欢迎来电查询](#)

商斯达中国传感器科技信息网：<http://www.sensor-ic.com/>

商斯达工控安防网：<http://www.pc-ps.net/>

商斯达电子元器件网：<http://www.sunstare.com/>

商斯达微波光电产品网：[HTTP://www.rfoe.net/](http://www.rfoe.net/)

商斯达消费电子产品网：<http://www.icasic.com/>

商斯达实业科技产品网：<http://www.sunstars.cn/> 微波元器件销售热线：

地址：深圳市福田区福华路福庆街鸿图大厦1602室

电话：0755-82884100 83397033 83396822 83398585

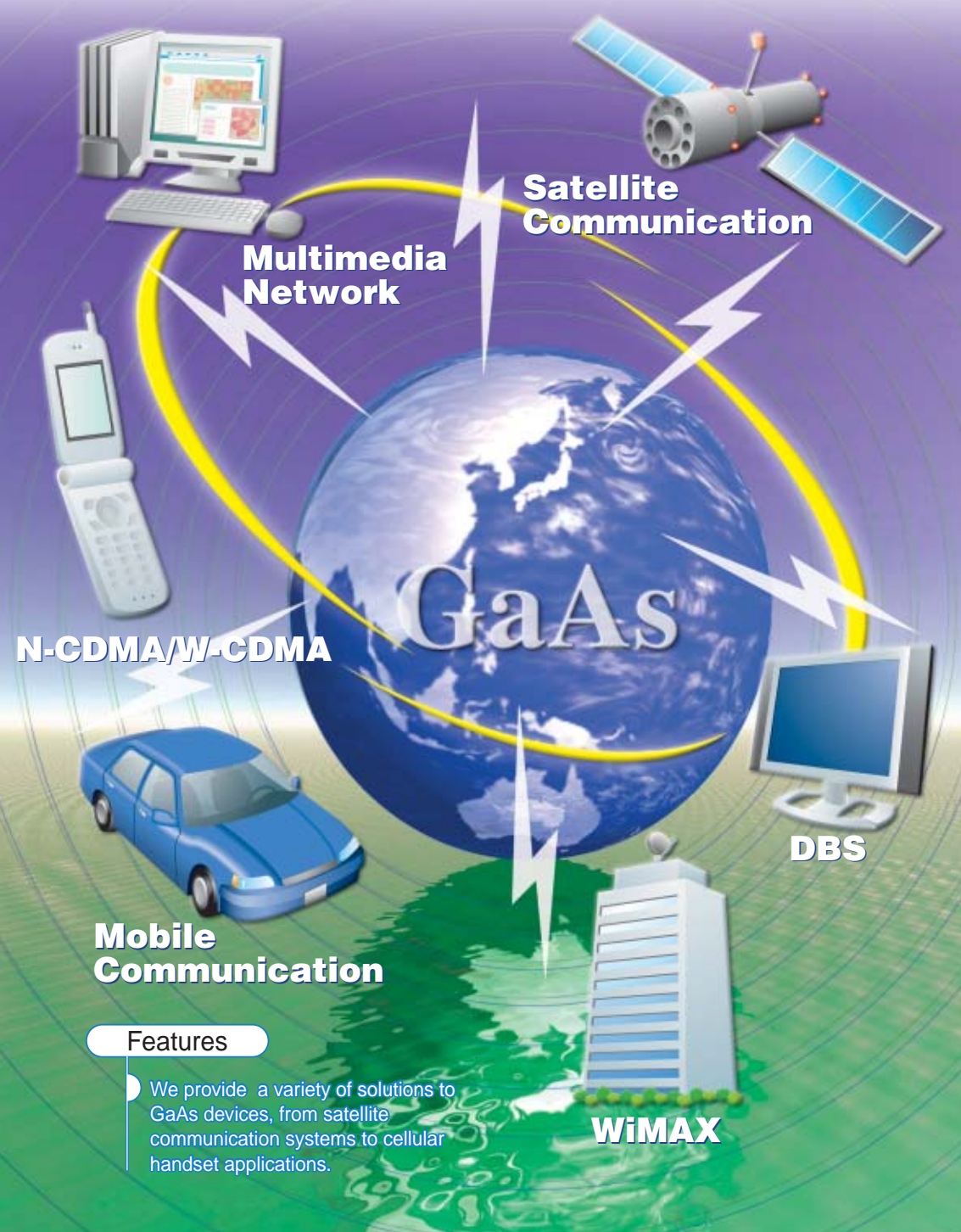
传真：0755-83376182 (0) 13823648918 MSN: SUNS8888@hotmail.com

邮编：518033 E-mail:szss20@163.com QQ: 195847376

深圳赛格展销部：深圳华强北路赛格电子市场2583号 电话：0755-83665529

技术支持: 0755-83394033 13501568376

**MITSUBISHI GaAs solutions
for communication networks
in the information era.**



Features

We provide a variety of solutions to GaAs devices, from satellite communication systems to cellular handset applications.

MAP FOR SELECTION 1

PRODUCTS 3

APPLICATION 7

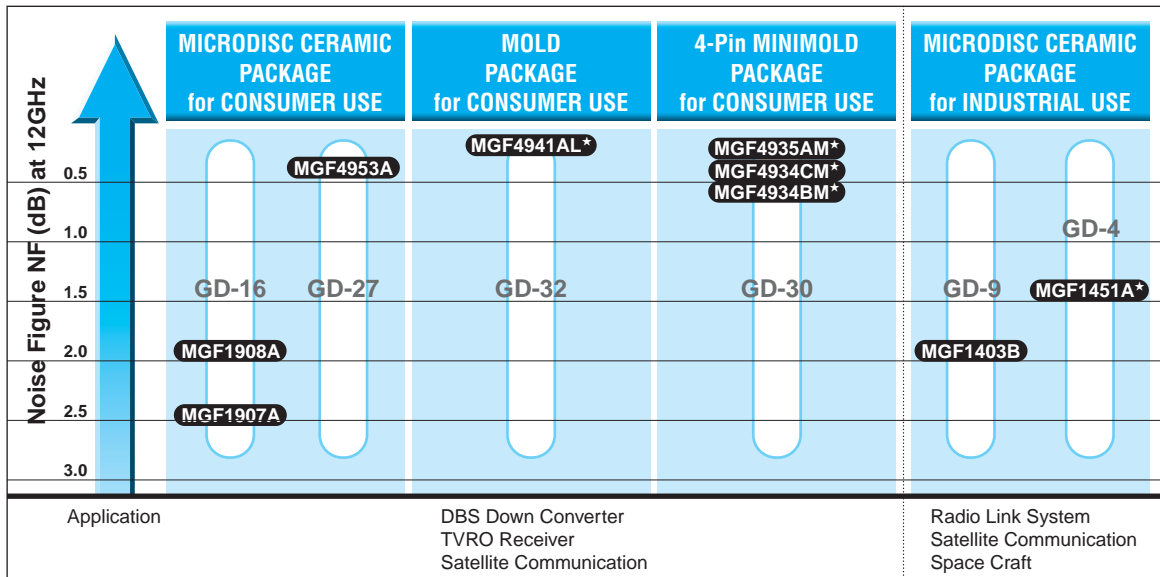
PACKAGE 9

MITSUBISHI GaAs devices: The best solution for realizing the information era.

Communication networks, such as high speed Internet, video-on-demand and high-speed data communication, are developing rapidly.

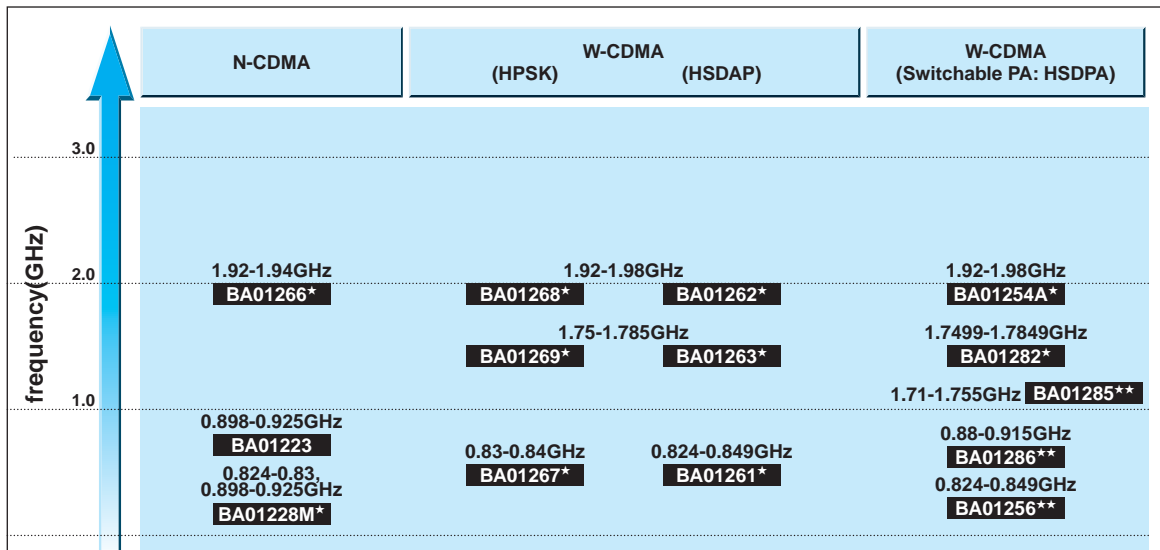
We are ready to offer the best solution to the systems for realizing the information era by providing a variety of GaAs products designed for satellite communication systems to base stations and cellular handset applications.

GaAs FET SERIES FOR MICROWAVE-BAND LOW-NOISE AMPLIFIERS



Note : MGF4xxx=HEMT MGF1xxx=MES FET
* : New Product

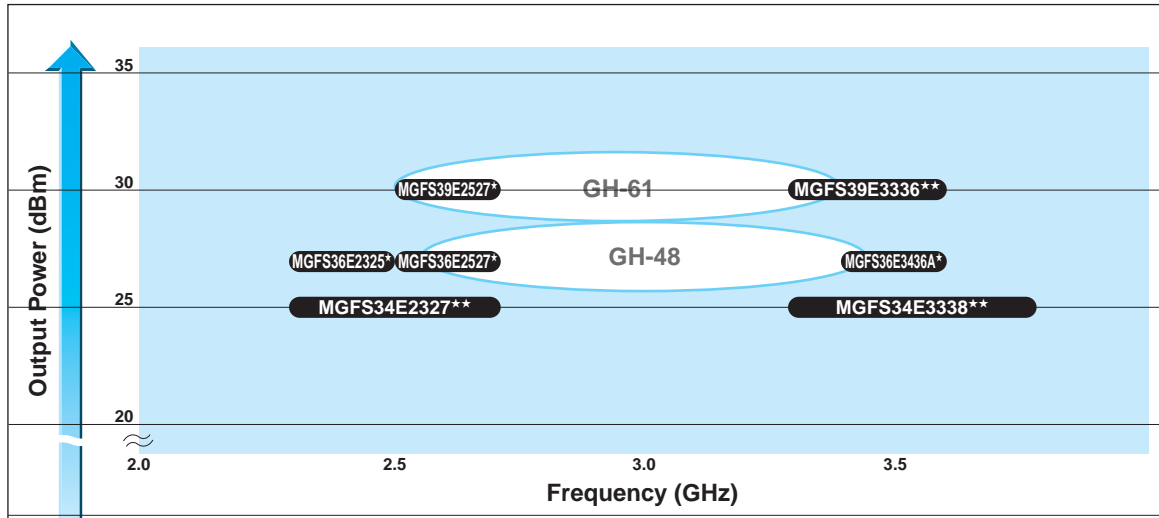
GaAs HYBRID IC FOR MOBILE PHONE



* : New Product ** : Under Development

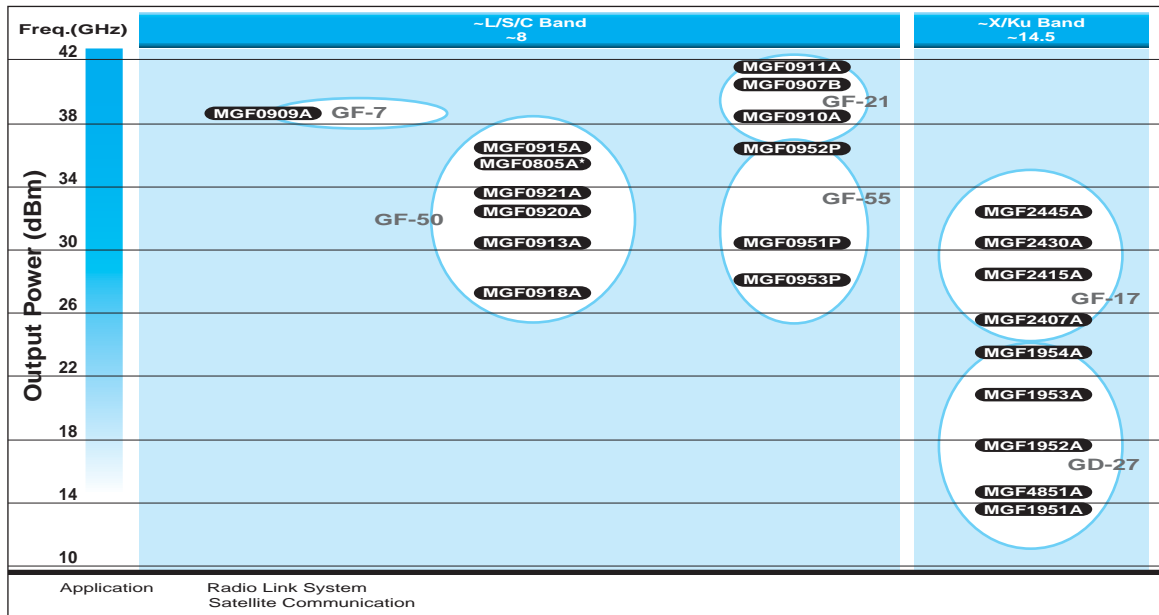
MAP For SELECTION

GaAs AMPLIFIER FOR WIRELESS ACCESS



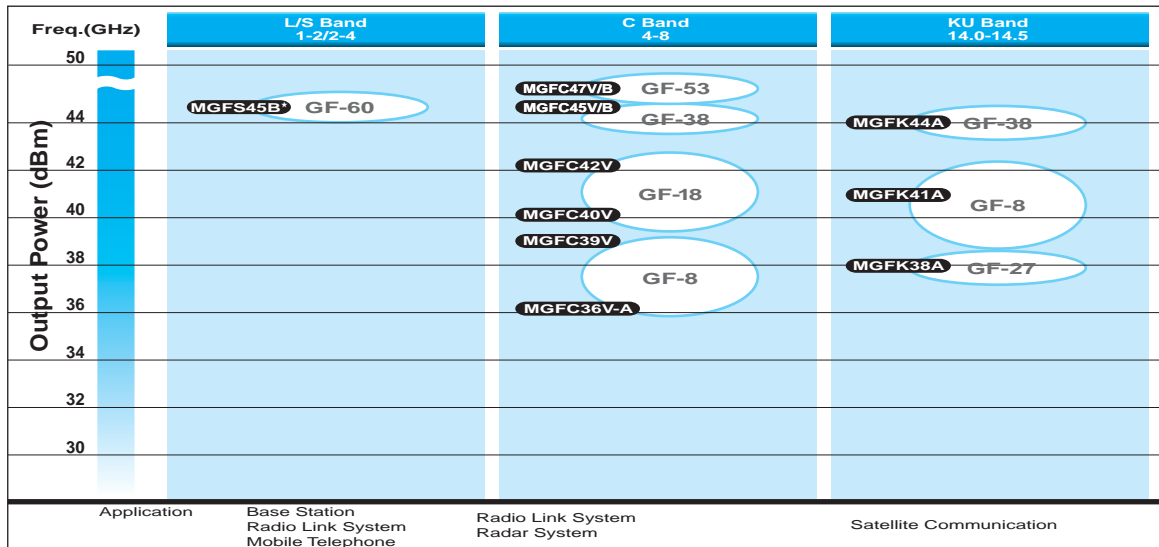
* : New Product ** : Under Development

GaAs FET FOR HIGH POWER DISCRETE



* : New Product

INTERNALLY MATCHED GaAs FET SERIES FOR MICROWAVE-BAND HIGH POWER AMPLIFIERS



* : New Product

GaAs FET SERIES FOR MICROWAVE- BAND LOW-NOISE AMPLIFIERS

Type Number	Noise Figure (dB)		Associated Gain (dB)		Frequency (GHz)	Drain-Source Voltage (V)	Drain Current (mA)	Package Outline
	Typ.	Max.	Min.	Typ.				
MGF1403B*	1.8	-	-	10.5	12	3	10	GD-9
MGF1907A	2.7	-	-	9	12	3	10	GD-16
MGF1908A	2	-	-	10.5	12	3	10	GD-16
MGF4941AL*	0.35	0.50	12.0	13.5	12	2	10	GD-32
MGF4953A	0.40	0.50	12.0	13.0	12	2	10	GD-27
MGF4931AM	0.60	0.80	10.0	11.5	12	2	7.5	GD-30
MGF4934BM*	0.50	0.80	11.5	12.5	12	2	10	GD-30
MGF4934CM*	0.50	0.75	11.5	13.0	12	2	10	GD-30
MGF4935AM*	0.45	0.65	11.0	12.0	12	2	10	GD-30
MGF4953B	0.55	0.80	9.0	10.5	20	2	10	GD-27
MGF4961B*	0.70	0.95	11.5	13.5	20	2	10	GD-31

Ta=25°C

* : Industrial Grade

* : New Product

GaAs FET SERIES FOR MICROWAVE- BAND HIGH-POWER AMPLIFIERS(Discrete Devices)

Type Number	Output Power at 1dB Gain Compression (dBm)		Output Power (dBm)	Linear Power Gain (dB)	3rd Order IM Distortion (dBc)		Power Added Efficiency (%)	Frequency (GHz)	Drain-Source Voltage (V)	Drain Current (A)	Thermal Resistance (°C/W)		Package Outline
	Min.	Typ.			Min.	Typ.					Typ.	Max.	
	MGF0907B*	38.5			40	-					8	-	
MGF0909A	37	38	-	10	-	-	45	2.3	10	1.3	-	-	GF-7
MGF0910A*	37	38	-	10	-	-	37	2.3	10	1.3	-	6	GF-21
MGF0911A*	40	41	-	10	-	-	40	2.3	10	2.6	-	4.5	GF-21
MGF0913A	-	-	29.5	11	-	-	48	1.9	10	0.2	20	30	GF-50
MGF0915A	-	-	35	13	-	-	50	1.9	10	0.8	5	8	GF-50
MGF0918A	-	-	25	18	-	-	45	1.9	10	0.15	35	50	GF-50
MGF0920A	-	-	30	16	-	-	45	1.9	10	0.4	13	18	GF-50
MGF0921A	-	-	31	15	-	-	40	1.9	10	0.5	11	15	GF-50
MGF0805A*	-	-	36.5	14.5	-	-	55	1.9	10	0.4	5	7	GF-50
MGF0951P	-	-	31	11	-	-42	50	2.15	10	0.2	20	25	GF-55
MGF0952P	-	-	36.5	11	-	-42	50	2.15	10	0.7	5	6	GF-55
MGF0953P	-	-	28	18	-	-	40	2.15	10	0.15	14	20	GF-55
MGF1451A**	11	13	-	10.5	-	-	-	12	3	0.03	-	-	GD-4
MGF1951A	11	13	-	7	-	-	-	12	3	0.03	-	-	GD-27
MGF1952A	15	17	-	5	-	-	-	12	3	0.06	-	-	GD-27
MGF1953A	18	20	-	4	-	-	-	12	4	0.1	-	-	GD-27
MGF1954A	21	23	-	3	-	-	-	12	6	0.1	-	-	GD-27
MGF2407A*	23	24.5	-	7	-	-	30	14.5	10	0.075	-	100	GF-17
MGF2415A*	26	27.5	-	6.5	-	-	29	14.5	10	0.15	-	60	GF-17
MGF2430A*	29	30.5	-	5.5	-	-	27	14.5	10	0.3	-	30	GF-17
MGF2445A*	31	32	-	5.5	-	-	20	12	10	0.45	-	15	GF-17
MGF4851A	12	14.5	-	9	-	-	-	12	2.5	0.025	-	-	GD-27

Ta=25°C

* : Industrial Grade

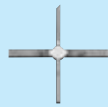
* : New Product

INTERNALLY MATCHED GaAs FET SERIES FOR WiMAX Base Station

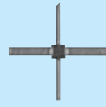
Type Number	Output Power at 1dB Gain Compression (dBm)		Output Power (dBm)	Linear Power Gain (dB)	3rd Order IM Distortion (dBc)		Power Added Efficiency (%)	Frequency (GHz)	Drain-Source Voltage (V)	Drain Current (A)	Thermal Resistance (°C/W)		Package Outline
	Min.	Typ.			Min.	Typ.					Typ.	Max.	
	MGFC36V3436	35			37	-					11	-42	
MGFC39V3436	38	39.5	-	10	-42	-45	32	3.4~3.6	10	2.4	3	3.5	GF-8
MGFC42V3436	41.5	42.5	-	12	-42	-45	37	3.4~3.6	10	4.5	-	1.9	GF-18
MGFC45B3436B*	-	-	45	11	-	-45	-	3.4~3.6	12	0.8	-	1.9	GF-60
MGFS45B2527B*	-	-	45	12	-	-45	-	2.5~2.7	12	0.9	-	1.9	GF-60
MGFC47B3436B*	-	-	47	10.5	-	-45	-	3.4~3.6	12	1.5	-	1.2	GF-60
MGFC47B3538B*	-	-	47	10.5	-	-45	-	3.5~3.8	12	1.5	-	1.2	GF-60

Ta=25°C

* : New Product



GD-4



GD-9



GD-16



GD-27



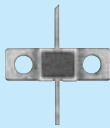
GD-30



GD-31



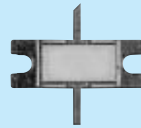
GD-32



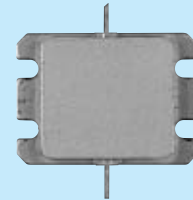
GF-7



GF-17



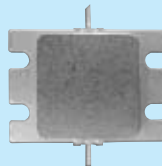
GF-21



GF-38



GF-50



GF-60



GF-55

INTERNALLY MATCHED GaAs FET SERIES FOR C BAND HIGH POWER AMPLIFIERS

Type Number	Output Power at 1dB Gain Compression(dBm)		Linear Power Gain(dB)	3rd Order IM Distortion(dBc)		Power Added Efficiency(%)	Frequency (GHz)	Drain-Source Voltage(V)	Drain Current (A)	Thermal Resistance (C/W)		Package Outline	Available Spec. No.
	Min.	Typ.		Min.	Typ.					Typ.	Max.		
MGFC36V4450A	35	37	9	-42	-45	32	4.4~5.0	10	1.2	5	6	GF-8	-51
MGFC36V5258	35	36	9	-42	-45	33	5.2~5.8	10	1.2	-	6	GF-8	-51
MGFC36V5964A	35	37	9	-42	-45	30	5.9~6.4	10	1.2	5	6	GF-8	-51
MGFC36V6472A	35	37	8	-42	-45	30	6.4~7.2	10	1.2	5	6	GF-8	-51
MGFC40V4450	39.5	40.5	9	-42	-45	32	4.4~5.0	10	2.4	-	3.5	GF-18	-51
MGFC40V5258	39.5	40.5	8	-42	-45	32	5.2~5.8	10	2.4	-	3.5	GF-18	-51
MGFC40V5964	39.5	40.5	8	-42	-45	30	5.9~6.4	10	2.4	3	3.5	GF-18	-51
MGFC40V6472	39.5	40.5	7	-42	-45	32	6.4~7.2	10	2.4	-	3.5	GF-18	-51
MGFC42V4450	41.5	42.5	9	-42	-45	32	4.4~5.0	10	4.5	-	1.9	GF-18	-51
MGFC42V5258	41.5	42.5	8	-	-	31	5.2~5.8	10	4.5	-	1.9	GF-18	-01
MGFC42V5964A	41.5	42.5	8	-42	-45	33	5.9~6.4	10	4.5	-	1.6	GF-38	-51
MGFC45V4450A	44	45	9	-	-45	34	4.4~5.0	10	8	0.8	1	GF-38	-01
MGFC45V5964A	44	45	8	-42	-45	33	5.9~6.4	10	8	0.8	1	GF-38	-51
MGFC47V5864	46	47	8.5	-	-	35	5.8~6.4	10	9.8	0.8	0.9	GF-53	-01
MGFC47A4450	46	47	9.5	-	-	40	4.4~5.0	10	9.8	0.8	0.9	GF-53	-01

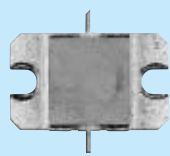
Ta=25°C

INTERNALLY MATCHED GaAs FET SERIES FOR X/Ku BAND HIGH POWER AMPLIFIERS

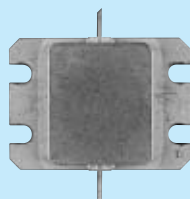
Type Number	Output Power at 1dB Gain Compression(dBm)		Linear Power Gain(dB)	Power Added Efficiency(%)	Frequency (GHz)	Drain-Source Voltage(V)	Drain Current (A)	Thermal Resistance (C/W)		Package Outline	Available Spec. No.
	Min.	Typ.						Typ.	Max.		
MGFK38A3745	37	38	7	30	13.75~14.5	10	1.5	3.6	4	GF-27	-01
MGFK41A4045	40	41	6	25	14.0~14.5	10	3	1.8	2.2	GF-8	-01
MGFK44A4045	43	44	5	17	14.0~14.5	10	6	1.2	1.5	GF-38	-01

Ta=25°C

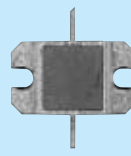
PRODUCT LIST



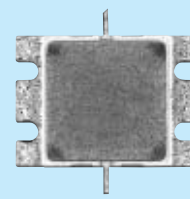
GF-8



GF-18



GF-27



GF-53



Type Number	Application	frequency (MHz)	Po(dBm)	Vcc(V)	Vref(V)	PAE(%)	Pin(dBm)	Package Outline
BA01223	N-CDMA	898~925	27.5	3.5	2.85	40	0	GH-46
BA01228M*	N-CDMA	824-830,898-925	28.0	3.5	2.85	37	1.0	GH-46
BA01266*	N-CDMA	1920~1940	27.5	3.5	2.85	42	1.0	GH-44
BA01267*	W-CDMA	830~840	26.5	3.5	2.90	47	-0.5	GH-44
BA01268*	W-CDMA	1920~1980	26.5	3.5	2.90	47	-1.5	GH-44
BA01269*	W-CDMA	1750~1785	26.5	3.5	2.90	47	-1.0	GH-44
BA01261*	W-CDMA(HSDPA)	824~849	26.5	3.5	2.90	39	-1.0	GH-44
BA01262*	W-CDMA(HSDPA)	1920~1980	26.5	3.5	2.90	42	-1.0	GH-44
BA01263*	W-CDMA(HSDPA)	1750~1785	26.5	3.5	2.90	43	-0.5	GH-44
BA01256**	W-CDMA(HSDPA)	824~849	27.5/16/8	3.4	-	38.5/24/7	2/-7/-14	GH-52
BA01286**	W-CDMA(HSDPA)	880~915	28.5/16/8	3.4	-	38/24/7	1.5/-6.5/-14	GH-52
BA01285**	W-CDMA(HSDPA)	1710~1755	27/16/8	3.4	-	37/22/6.5	0/-6.5/-14	GH-51
BA01282*	W-CDMA(HSDPA)	1749.9-1784.9	27/16/8	3.4	-	35/21/6	0/-6/-13.5	GH-51
BA01254A*	W-CDMA(HSDPA)	1920~1980	27/16/8	3.4	-	38/24/7	0/-5.5/-13	GH-51

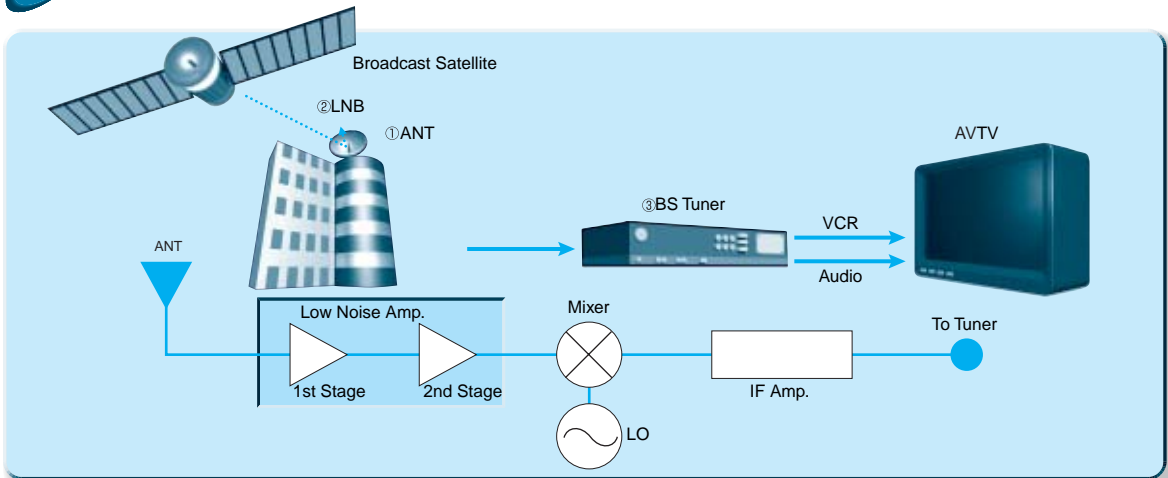
* : New Product ** : Under Development



Type Number	Frequency (MHz)	Pout & EVM	Gain(dB)	Vcc(V)	Vref(V)	PAE(%)	Package Outline
MGFS34E2327**	2.3~2.7	25dBm@2.5%	35	3.3	2.85	20	-
MGFS34E3338**	3.3~3.8	25dBm@2.5%	30	3.3	2.85	20	-
MGFS36E2325*	2.3~2.5	27dBm@2.5%	33	6	2.85	11	GH-48
MGFS36E2527*	2.5~2.7	27dBm@2.5%	33	6	2.85	12	GH-48
MGFS36E3436A*	3.4~3.6	27dBm@4.0%	30	6	2.85	11	GH-48
MGFS39E2527*	2.5~2.7	30dBm@2.5%	43	6	2.85	12	GH-61
MGFS39E3336**	3.3~3.6	30dBm@2.5%	40	6	2.85	13	GH-61

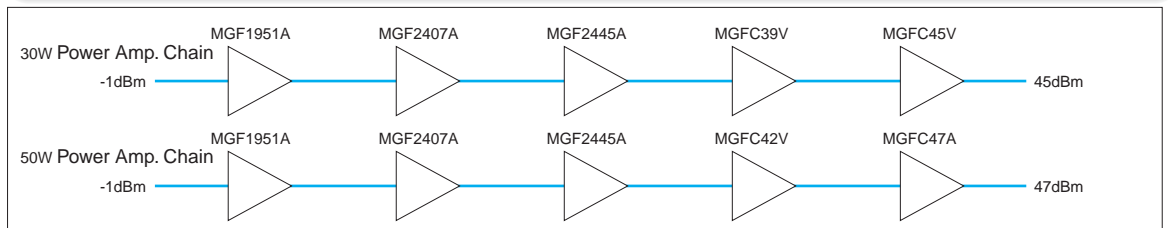
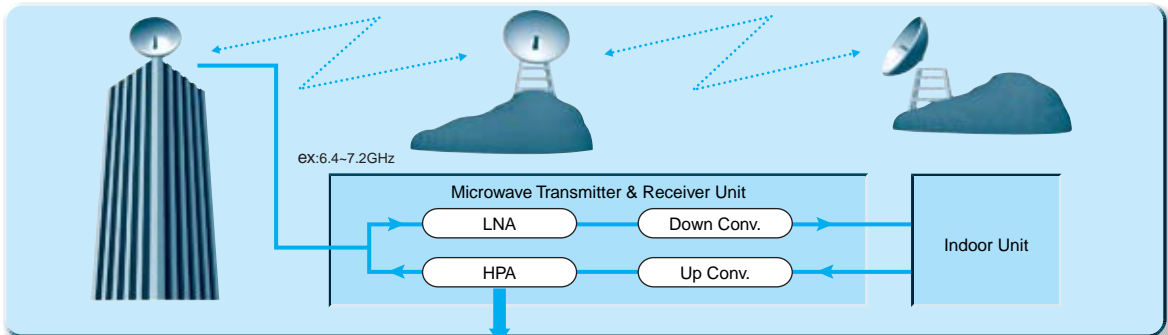
* : New Product ** : Under Development

Lineup for 12GHz -Band LNB

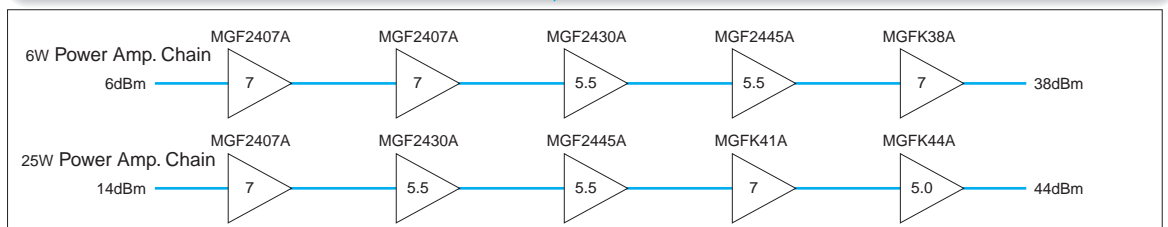
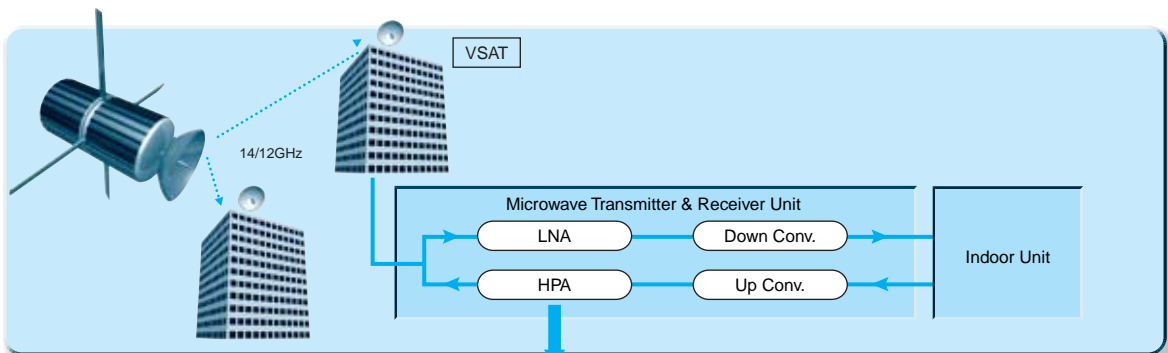


Performance of LNB	1st Stage	2nd Stage	Mixer
Low Noise Model	MGF4941AL	MGF4941AL	MGF4934CM
Standard Model	MGF4935AM	MGF4934CM	MGF4934CM

Lineup for Microwave Links



Lineup for Satellite Communication



Application Note

		Title	Date
GaAs Transistors	f=1.9GHzband	RF characteristics data of MGF0915A for Freq=1.85-1.95GHz band	May./2005
		RF characteristics data of MGF0921A for Freq=1.85-1.95GHz band	May./2005
		RF characteristics data of MGF0951P for Freq=1.85-1.95GHz band	May./2005
		RF characteristics data of MGF0952P for Freq=1.85-1.95GHz band	May./2005
	f=2.1GHzband	RF characteristics data of MGF0906B for Freq.=2.11-2.17GHz band	Apr./2005
		RF characteristics data of MGF0907B for Freq.=2.11-2.17GHz band	Apr./2005
		RF characteristics data of MGF0915A for Freq=2.11-2.17GHz band	May./2005
		RF characteristics data of MGF0921A for Freq=2.11-2.17GHz band	May./2005
		RF characteristics data of MGF0951P for Freq=2.11-2.17GHz band	May./2005
		RF characteristics data of MGF0952P for Freq=2.11-2.17GHz band	May./2005
	f=2.35GHz band	RF characteristics data of MGF0915A for Freq=2.3-2.4GHz band	May./2005
		RF characteristics data of MGF0921A for Freq=2.3-2.4GHz band	May./2005
		RF characteristics data of MGF0951P for Freq=2.3-2.4GHz band	May./2005
		RF characteristics data of MGF0952P for Freq=2.3-2.4GHz band	May./2005
	f=2.6GHzband	RF characteristics data of MGF0915A for Freq=2.5-2.6GHz band	May./2005
		RF characteristics data of MGF0921A for Freq=2.5-2.6GHz band	May./2005
RF characteristics data of MGF0951P for Freq=2.5-2.6GHz band		May./2005	
RF characteristics data of MGF0952P for Freq=2.5-2.6GHz band		May./2005	

High Frequency Devices Naming System

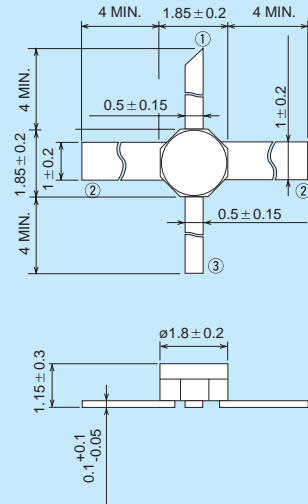
■ GaAs FET(Discrete)
MGF 1403 BX
 ● Quality Grade X : IGX
 V : IGV

■ Internally Matched GaAs FET
MGF C 36 V 5964
 ● Freq. Band : L, S, C, X, K, Ku
 ● Typical Output power in dBm
 ex.36=36dBm=4W(typ.)
 ● Internally Matched : V, A
 Multi Stage FET Amp : H
 Multi Stage HBT Amp : E
 ● Freq. Band in GHz
 ex.5964=5.9~6.4GHz

■ GaAs Hybrid IC
FA 01 2 34
 ● Device Structure : FA(FET), BA(Bipolar Transistor)
 ● Freq. Band in GHz
 ● Stage Number
 ● Series Number

GD-4

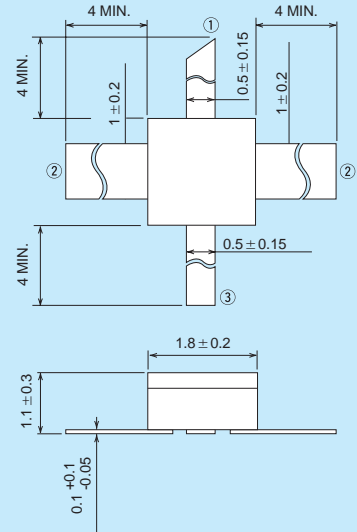
① Gate ③ Drain
② Source



Unit:mm

GD-9

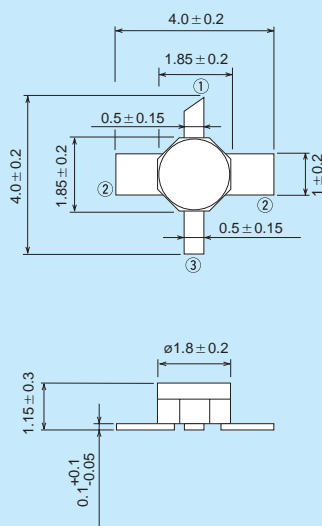
① Gate ③ Drain
② Source



Unit:mm

GD-16

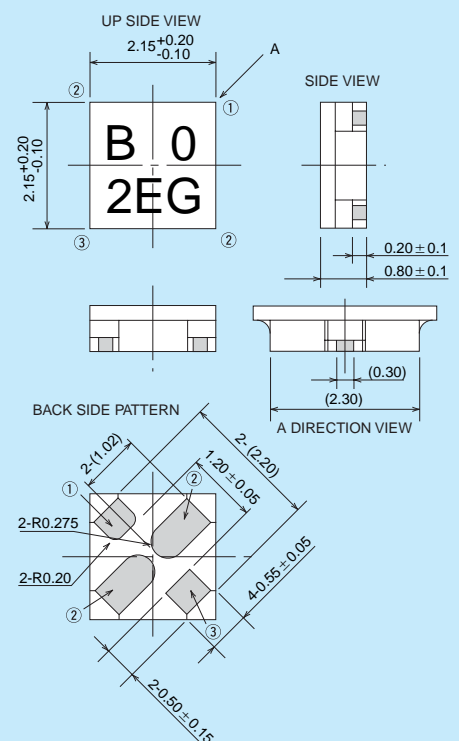
① Gate ③ Drain
② Source



Unit:mm

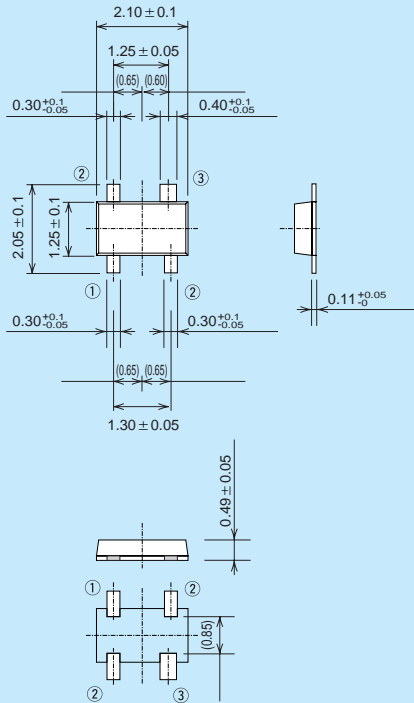
GD-27

① Gate ③ Drain
② Source



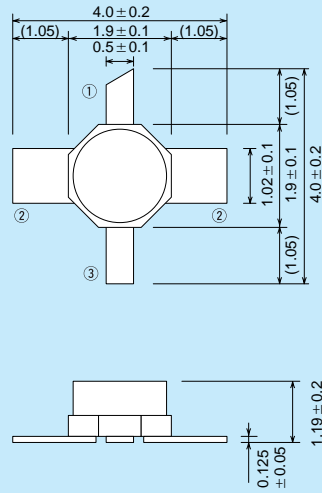
Unit:mm

GD-30 ①Gate ③Drain ②Source



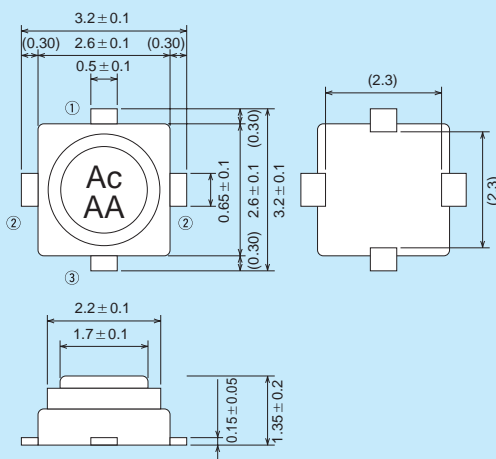
Unit:mm

GD-31 ①Gate ③Drain ②Source



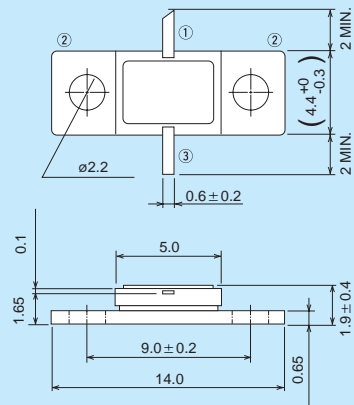
Unit:mm

GD-32 ①Gate ③Drain ②Source



Unit:mm

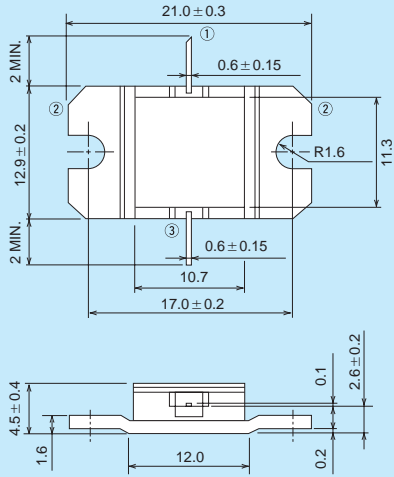
GF-7 ①Gate ③Drain ②Source



Unit:mm

GF-8

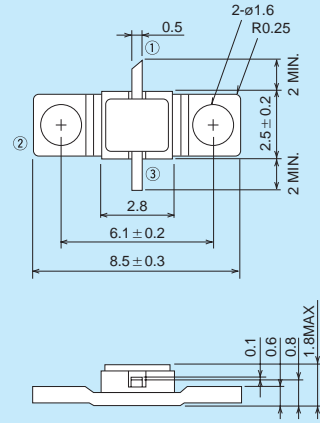
① Gate ③ Drain
② Source



Unit:mm

GF-17

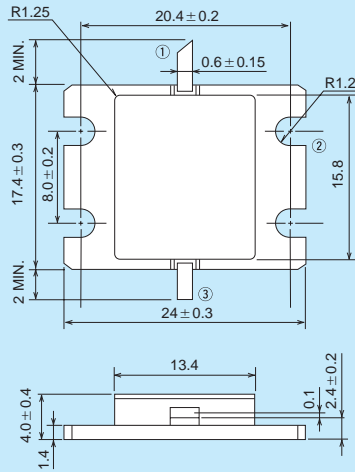
① Gate ③ Drain
② Source



Unit:mm

GF-18

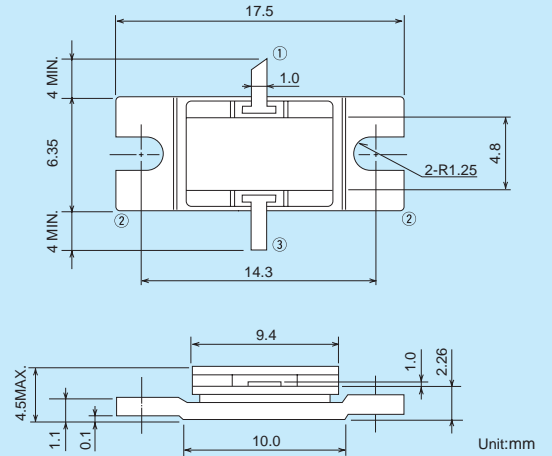
① Gate ③ Drain
② Source



Unit:mm

GF-21

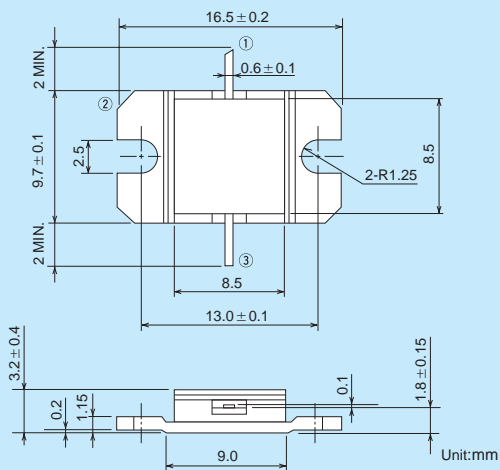
① Gate ③ Drain
② Source



Unit:mm

GF-27

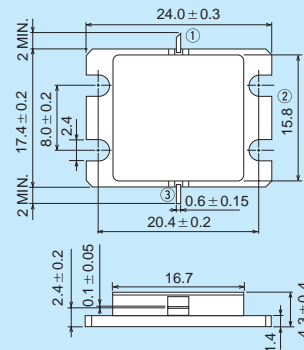
① Gate ③ Drain
② Source



Unit:mm

GF-38

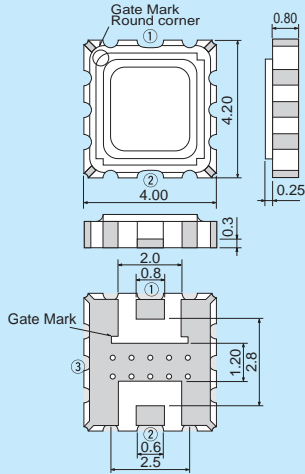
① Gate ③ Drain
② Source



Unit:mm

GF-50

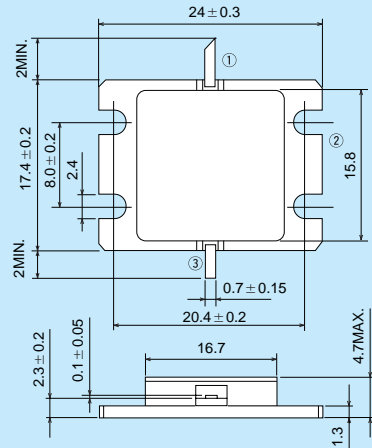
① Gate ③ Drain
② Source



Unit:mm

GF-53

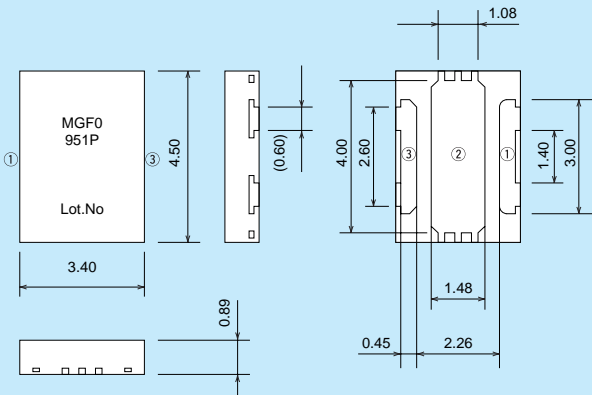
① Gate ③ Drain
② Source



Unit:mm

GF-55

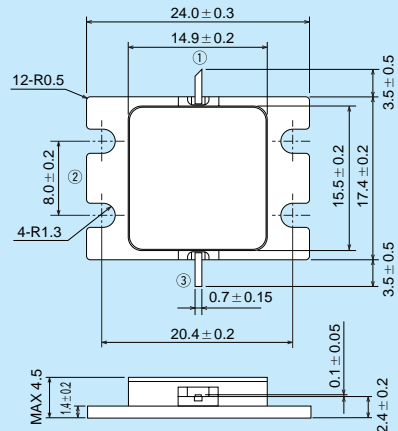
① Gate ③ Drain
② Source



Unit:mm

GF-60

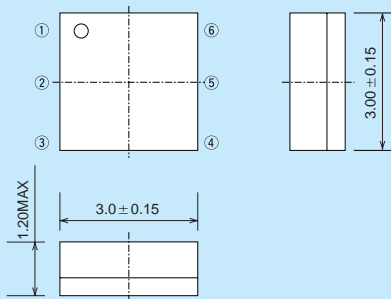
① Gate ③ Drain
② Source



Unit:mm

GH-44

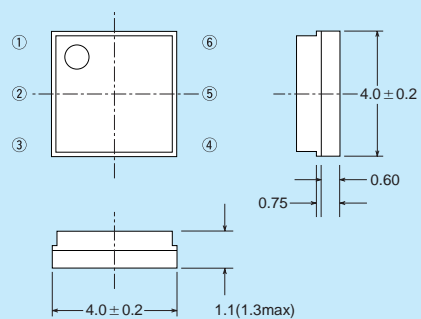
① Pin ③ Vc2 ⑤ Vcb ⑦ GND
② Vc1 ④ Pout ⑥ Vref



Unit:mm

GH-46

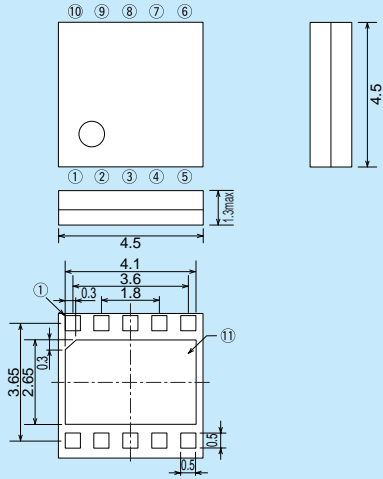
① Pin ③ Vc2 ⑤ Vcb ⑦ GND
② Vc1 ④ Pout ⑥ Vref



Unit:mm

GH-48

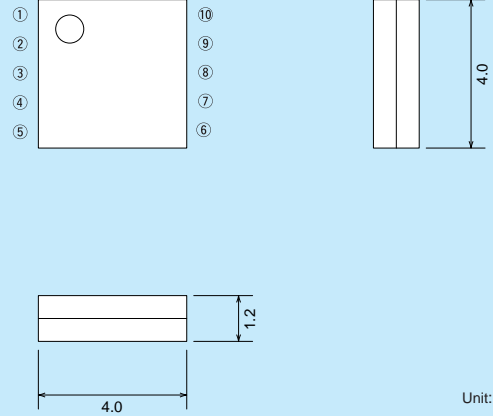
- ① Pin ④ Vc2 ⑦ Vdet ⑩ Vcont
- ② Vcb ⑤ Vc3 ⑧ GND ⑪ GND
- ③ Vc1 ⑥ Pout ⑨ Vref



Unit:mm
tolerance:+/-0.2

GH-51

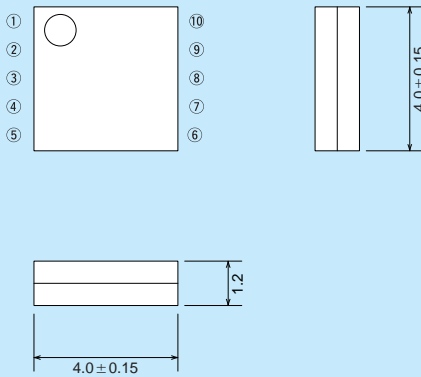
- ① Vbias ④ Vmode0 ⑦ GND ⑩ Vcc
- ② Pin ⑤ Venable ⑧ Pout ⑪ GND
- ③ Vmode1 ⑥ GND ⑨ GND



Unit:mm

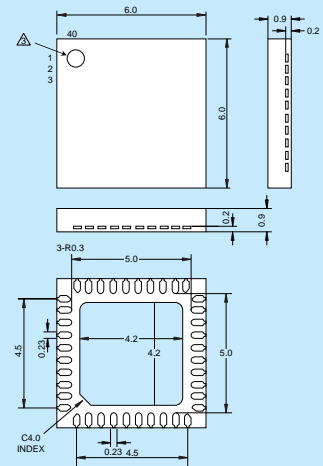
GH-52

- ① Venable ④ Pin ⑦ GND ⑩ GND
- ② Vmode0 ⑤ Vbias ⑧ Pout ⑪ GND
- ③ Vmode1 ⑥ Vcc ⑨ GND



Unit:mm

GH-61



Unit:mm

SUNSTAR 商斯达实业集团是集研发、生产、工程、销售、代理经销、技术咨询、信息服务等为一体的高科技企业，是专业高科技电子产品生产厂家，是具有10多年历史的专业电子元器件供应商，是中国最早和最大的仓储式连锁规模经营大型综合电子零部件代理分销商之一，是一家专业代理和分销世界各大品牌IC芯片和电子元器件的连锁经营综合性国际公司，专业经营进口、国产名厂名牌电子元件，型号、种类齐全。在香港、北京、深圳、上海、西安、成都等全国主要电子市场设有直属分公司和产品展示展销窗口门市部专卖店及代理分销商，已在全国范围内建成强大统一的供货和代理分销网络。我们专业代理经销、开发生产电子元器件、集成电路、传感器、微波光电元器件、工控机/DOC/DOM电子盘、专用电路、单片机开发、MCU/DSP/ARM/FPGA软件硬件、二极管、三极管、模块等，是您可靠的一站式现货配套供应商、方案提供商、部件功能模块开发配套商。商斯达实业公司拥有庞大的资料库，有数位毕业于著名高校——有中国电子工业摇篮之称的西安电子科技大学（西军电）并长期从事国防尖端科技研究的高级工程师为您精挑细选、量身订做各种高科技电子元器件，并解决各种技术问题。

微波光电部专业研制、代理经销高频、微波、光纤、光电元器件、组件、部件、模块、整机；电磁兼容元器件、材料、设备；微波CAD、EDA软件、开发测试仿真工具；微波、光纤仪器仪表。欢迎国外高科技微波、光纤厂商将优秀产品介绍到中国、共同开拓市场。长期大量现货专业批发高频、微波、卫星、光纤、电视、CATV器件：晶振、VCO、连接器、PIN开关、变容二极管、开关二极管、低噪晶体管、功率电阻及电容、放大器、功率管、MMIC、混频器、耦合器、功分器、振荡器、合成器、衰减器、滤波器、隔离器、环行器、移相器、调制解调器；光电子元件和组件：红外发射管、红外接收管、光电开关、光敏管、发光二极管和发光二极管组件、半导体激光二极管和激光器组件、光电探测器和光接收组件、光发射接收模块、光纤激光器和光放大器、光调制器、光开关、DWDM用光发射和接收器件、用户接入系统光收发器件与模块、光纤连接器、光纤跳线/尾纤、光衰减器、光纤适配器、光隔离器、光耦合器、光环行器、光复用器/转换器；无线收发芯片和模组、蓝牙芯片和模组。

更多产品请看本公司产品专用销售网站：[欢迎索取免费详细资料、设计指南和光盘；产品凡多，未能尽录，欢迎来电查询](#)

商斯达中国传感器科技信息网：<http://www.sensor-ic.com/>

商斯达工控安防网：<http://www.pc-ps.net/>

商斯达电子元器件网：<http://www.sunstare.com/>

商斯达微波光电产品网：[HTTP://www.rfoe.net/](http://www.rfoe.net/)

商斯达消费电子产品网：<http://www.icasic.com/>

商斯达实业科技产品网：<http://www.sunstars.cn/> 微波元器件销售热线：

地址：深圳市福田区福华路福庆街鸿图大厦1602室

电话：0755-82884100 83397033 83396822 83398585

传真：0755-83376182 (0) 13823648918 MSN: SUNS8888@hotmail.com

邮编：518033 E-mail:szss20@163.com QQ: 195847376

深圳赛格展销部：深圳华强北路赛格电子市场2583号 电话：0755-83665529

技术支持: 0755-83394033 13501568376